(TI P633)

OFFICE MACHINE.

HOUSEHOLD USE EQUIPMENT.

SOLID STATE RELAY.

SWITCHING POWER SUPPLY.

The TOSHIBA TLP633 and TLP634 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

TLP634 is no-base internal connection for high-EMI environments.

Collector-emitter Voltage 55V (Min.) Current Transfer Ratio 50% (Min.)

Rank GB 100% (Min.)

UL Recognized UL1577, File No. E67349

BSI Approved BS415:1990, BS7002:1989

(EN60950)

Certificate No. 7123, 7437

SEMKO Approved SS4330784.

Certificate No. 8937148 (TLP633)

9019123 (TLP634)

Isolation Voltage 4000V_{rms} (Min.)

Option (D4) type

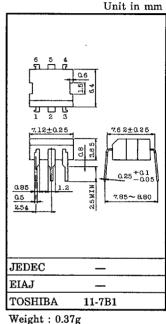
VDE Approved DIN VDE0884/08.87.

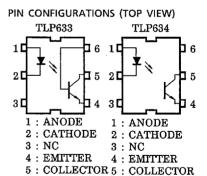
Certificate No. 68367

Maximum Operating Insulation Voltage 630Vpk Highest Permissible Over Voltage 6000vpk

(Note) When a VDEO884 approved type is needed, Please designate the "option (D4)"

			7.62mm pich standard type	10.16mm pich (LF2) type
•	Creepage Distance	:	7.0mm (Min)	8.0mm (MIn)
	Clearance	:	7.0mm (Min)	8.0mm (Min)
	Internal Creepage Path	:	4.0mm (Min)	4.0mm (Min)
	Insulation Thickness	:	0.5mm (Min)	0.5mm (Min)





6: BASE 6 : NC

-755 -

(TLP633)

Current Transfer Ratio

TYPE	CLASSI- FICATION	CURRENT TRANSFER RATIO (%) (IC/IF) IF=5mA, VCE=5V, Ta=25°C		MARKING OF CLASSIFICATION
	*1	MIN.	=5V, Ta=25 C	
	(None)	50	600	BLANK, Y, Y, G, G, B, B, GB
TLP633		50	150	Y, Y■
	Rank GR	100	300	G, G ■
TLP634		200 600		B, B [■]
	Rank GB	100	600	G, G [■] , B, B [■] , GB

*1 : Ex. Rank GB : TLP633 (GB)

Note : Application type name for certification test, please use standard product type

name, i. e.

TLP633 (GB) : TLP633

MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
	Forward Current	$I_{\mathbf{F}}$	60	mA
A	Forward Current Derating (Ta≥39°C)	ΔI _F /°C	-0.7	mA/°C
田	Peak Forward Current (100 µs pulse, 100 pps)	I _{FP}	1	A
T	Reverse Voltage	V_{R}	5	v
	Junction Temperature	T_{j}	125	°C
	Collector-Emitter Voltage	v_{CEO}	55	V
24	Collector-Base Voltage (TLP633)	V _{CBO}	80	v
T 0	Emitter-Cllector Voltage	v_{ECO}	7	V
ြ	Emitter-Base Voltage (TLP633)	$v_{ m EBO}$	7	V
TE	Collector Current	$I_{\mathbf{C}}$	50	mA
闰	Power Dissipation	$P_{\mathbf{C}}$	150	mW
ū	Power Dissipation Derating (Ta≥25°C)	ΔP _C /°C	-1.5	mW/°C
	Junction Temperature	T_{j}	125	°C
Sto	rage Temperature Range	$T_{ m stg}$	-55~150	°C
Op	erating Temperature Range	$T_{ m opr}$	-55~100	°C
Lea	ad Soldering Temperature (10 s)	T _{sol}	260	°C
Tot	al Package Power Dissipation	PT	250	mW
Tot	al Package Power Dissipation Derating (Ta≥25°C)	ΔP _T /°C	-2.5	mW/°C
Iso	lation Voltage (AC, 1min., RH≦60%) (Note 1)	BVS	4000	Vrms

Note 1: Device considered a two-terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

(TLP633)
INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
l _a	Forward Voltage	$v_{\mathbf{F}}$	$I_{ m F} = 10 { m mA}$	1.0	1.15	1.3	V
臼	Reverse Current	$I_{\mathbf{R}}$	$V_R = 5V$	_	_	10	μ A
1	Capacitance	C_{T}	V=0, $f=1MHz$	_	30	_	pF
	Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{\hbox{\scriptsize C}}\!=\!0.5 \hbox{\scriptsize mA}$	55	_	_	v
	Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	$I_{\text{E}} = 0.1 \text{mA}$	7	_	_	v
	Collector-Base Breakdown Voltage (TLP633)	V _{(BR)CBO}	$I_{\text{C}} = 0.1 \text{mA}$	80	_	-	v
CTOR	Emitter-Base Breakdown Voltage (TLP633)	V _{(BR)EBO}	IE=0.1mA	7	_	_	V
回	Collector Dark Current	ICEO	$V_{CE} = 24V$		10	100	nA
E			$V_{CE} = 24V$, $Ta = 85$ °C	_	2	50	μA
A	Collector Dark Current (TLP633)	ICER	$V_{\text{CE}} = 24\text{V}, \text{ Ta} = 85^{\circ}\text{C}$ $R_{\text{BE}} = 1\text{M}\Omega$	_	0.5	10	μ A
	Collector Dark Current (TLP633)	ICBO	$V_{\mathrm{CB}} = 10\mathrm{V}$	_	0.1	_	nA
	DC Foward Current Gain (TLP633)	hFE	$V_{\rm CE}$ =5V, IC=0.5mA	_	400		_
	Capacitance Collector to Emitter	CCE	V=0, f=1MHz		10	_	рF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	$I_{ m C}/I_{ m F}$	$I_{F=5mA}$, $V_{CE}=5V$	50	_	600	%
Current Transfer Italio	1C/1F	Rank GB	100	_	600	10
Saturated CTR	IC/IF(sat)	$I_F=1mA$, $V_{CE}=0.4V$	_	60	_	%
Saturated CTK		Rank GB	30	_	_	70
Base Photo-Current	I_{PB}	I _F =5mA, V _{CB} =5V		10	_	μ A
Collector-Emitter		I _C =2.4mA, I _F =8mA			0.4	
	VCE (sat)	I _C =0.2mA, I _F =1mA		0.2		v
Saturation Voltage	-	Rank GB			0.4	

(TLP633)

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	c_{S}	$V_S=0$, $f=1MHz$		0.8		pF
Isolation Resistance	RS	V _S =500V	5×10 ¹⁰	1014	_	Ω
	BVS	AC, 1minute	4000	_		
Isolation Voltage		AC, 1second, in oil	_	10000	_	Vrms
		DC, 1minute, in oil	_	10000		Vdc

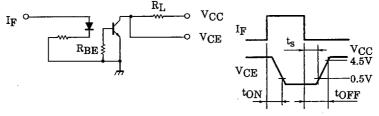
SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr			2	_	
Fall Time	tf	$V_{CC}=10V$	_	3	_	
Turn-on Time	ton	$I_{C}=2mA$ $R_{L}=100\Omega$	_	3	10	μS
Turn-off Time	tOFF	11, -10012	_	3	10	
Turn-on Time	ton	$R_{L}=1.9k\Omega$ (Fig.1)		3	l –	
Storage Time	t _s	R _{BE} =OPEN		40		μs
Turn-off Time	tOFF	$V_{CC}=5V$, $I_F=16mA$	_	90	_	
Turn-on Time	ton	R _L =1.9kΩ (Fig.1)	_	. 3		
Storage Time	t _s	$R_{BE} = 220 k\Omega \text{ (TLP633)}$	_	30	_	μ\$
Turn-off Time	tOFF	V _{CC} =5V, I _F =16mA	_	60	_	

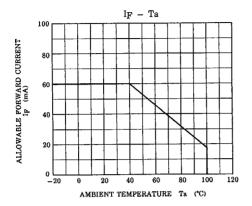
RECOMMENDED OPERATING CONDITIONS

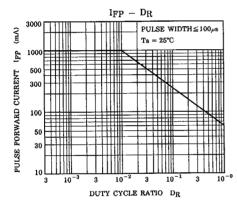
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	v_{CC}		5	24	v
Forward Current	$I_{\mathbf{F}}$	_	16	25	mA
Collector Current	IC	-	1	10	mA
Operating Temperature	Topr	-25		85	°C

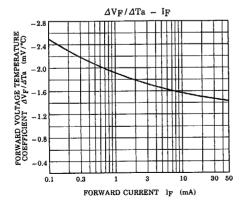
Fig. 1 SWITCHING TIME TEST CIRCUIT

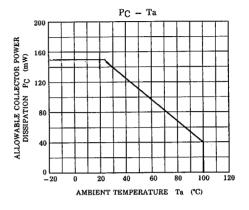


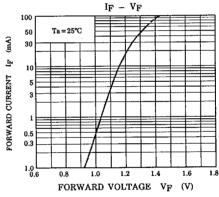
(TLP633)

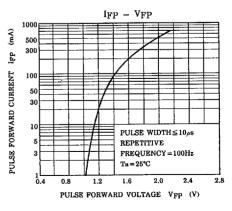




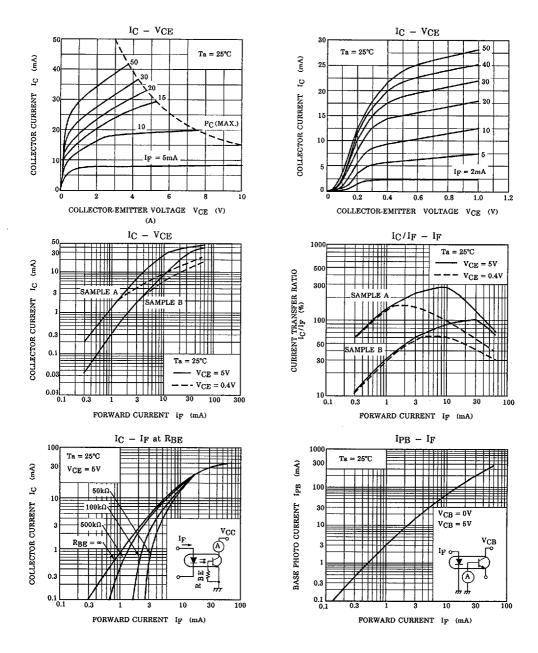








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